

Supplementary Materials: Melioration of Electrical and Optical Properties of Al and B Co-Doped ZnO Transparent Semiconductor Thin Films

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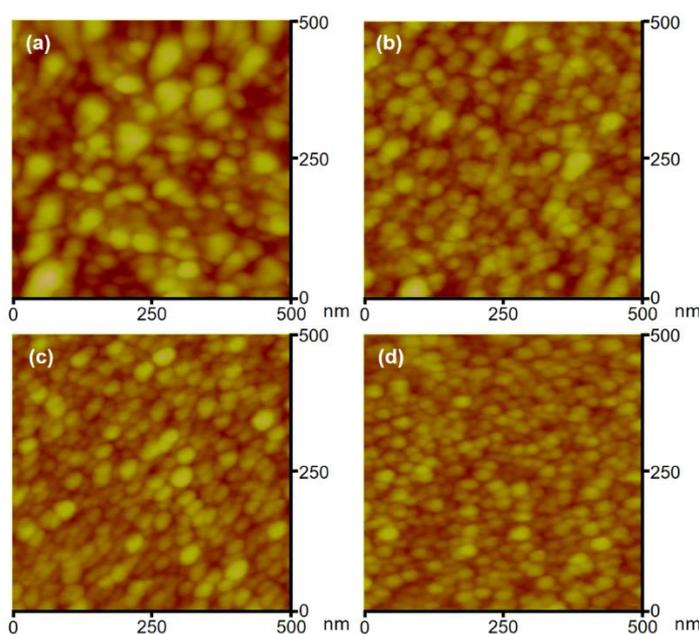


Figure S1. 2-D topographical SPM images of ZnO-based thin films: (a) ZnO, (b) ZnO:Al, (c) ZnO:Al-1% B, and (d) ZnO:Al-2% B samples.

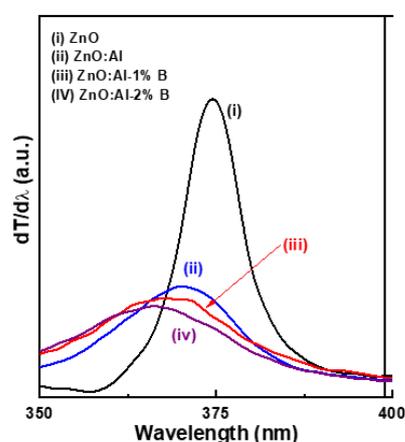


Figure S2. Plot of the first derivative of optical transmittance with respect to wavelength ($dT/d\lambda$) versus wavelength in the near-UV region for the ZnO-based thin film samples.